



100V N-Channel Enhancement Mode MOSFET

Voltage

100 V

Current

42A

Features

- RDS(ON), VGS@10V, ID@20A<25mΩ
- RDS(ON), VGS@4.5V, ID@15A<28.5mΩ
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

- Case: DFN5060-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0028 ounces, 0.08 grams
- Marking: Q5476AL

DFN5060-8L

Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	100	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C		42		
	T _C =100°C	l _D	26.6	А	
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	150		
Power Dissipation	T _C =25°C	Po	83	W	
	T _C =100°C		33		
Continuous Drain Current	T _A =25°C	I _D	6.5	Α	
	T _A =70°C		5.2	Α	
Power Dissipation	T _A =25°C	D-	2.0	W	
	T _A =70°C	Po	1.3		
Single Pulse Avalanche Energy ^(Note 6)		E _{AS}	63.4	mJ	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	1.5	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	100	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.0	1.8	2.5	V		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =20A	-	20	25	mΩ		
		V _{GS} =4.5V,I _D =15A	-	22	28.5			
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =80V, V_{GS} =0V	-	-	1.0	uA		
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA		
Dynamic (Note 7)		T						
Total Gate Charge	Q_{g}	V _{DS} =50V, I _D =10A, V _{GS} =10V ^(Note 1,2)	-	31	-	nC		
Gate-Source Charge	Q_gs		-	5.1	-			
Gate-Drain Charge	Q_{gd}		-	7.3	-			
Input Capacitance	Ciss	V _{DS} =30V, V _{GS} =0V, f=1.0MHZ	-	1519	-	pF		
Output Capacitance	Coss		-	132	-			
Reverse Transfer Capacitance	Crss	I=1.0IVII IZ	-	66	-			
Turn-On Delay Time	td _(on)	V_{DD} =50V, I_{D} =10A, V_{GS} =10V, R_{G} =3 Ω (Note 1,2)	-	11	-			
Turn-On Rise Time	t _r		-	42	-	ns		
Turn-Off Delay Time	td _(off)		-	40	-			
Turn-Off Fall Time	t _f	K _G =322	-	19	-			
Drain-Source Diode								
Maximum Continuous Drain-Source	I ₋				42	Α		
Diode Forward Current	I _S		-	-	44	^		
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	0.7	1.2	V		

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=3mH, I_{AS} =6.5A, V_{DD} =50V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

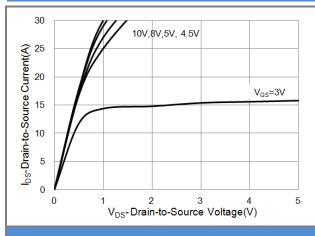


Fig.1 Output Characteristics

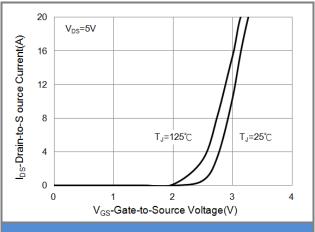


Fig.2 Transfer Characteristics

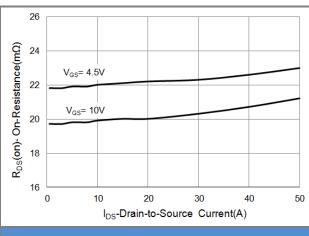


Fig.3 On-Resistance vs. Drain Current

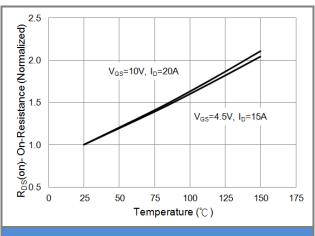
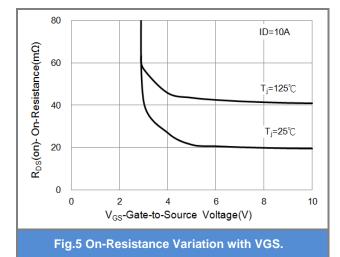
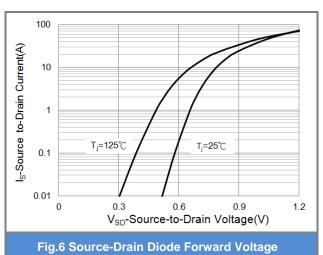


Fig.4 On-Resistance vs. Junction temperature









TYPICAL CHARACTERISTIC CURVES

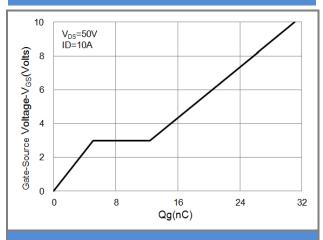


Fig.7 Gate-Charge Characteristics

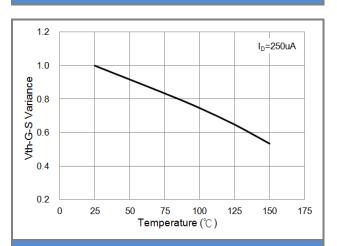
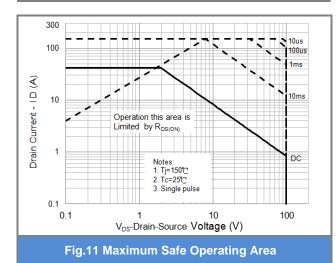


Fig.9 Threshold Voltage Variation with Temperature



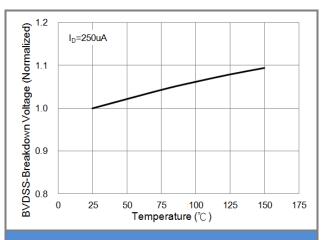


Fig.8 Breakdown Voltage Variation vs. Temperature

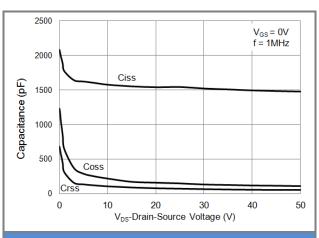


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

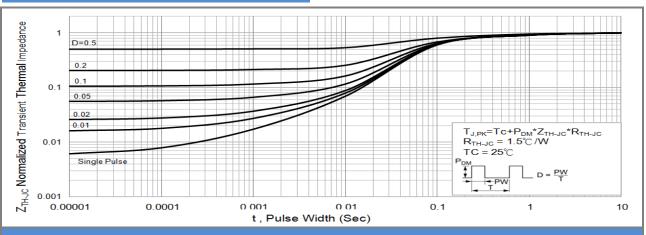


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

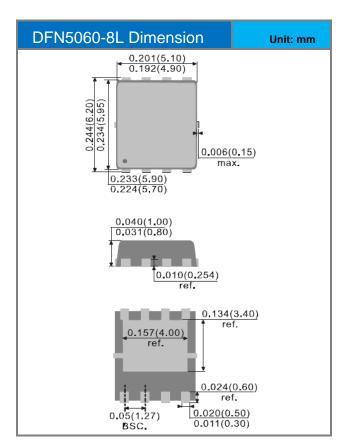


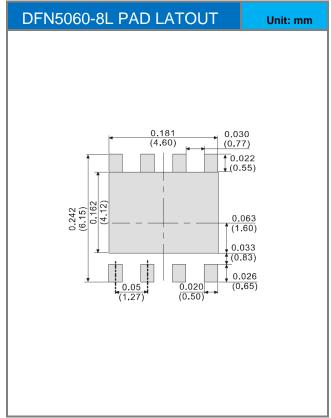


PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	king type Marking	
PJQ5476AL_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5476AL	Halogen free

Packaging Information & Mounting Pad Layout









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